



11) Publication number:

0 627 768 A3

(2) EUROPEAN PATENT APPLICATION

(21) Application number: 94108463.4 (51) Int. Cl.⁶: H01L 29/812

22 Date of filing: 01.06.94

Priority: 01.06.93 JP 130481/93

Date of publication of application:07.12.94 Bulletin 94/49

Designated Contracting States:
DE FR GB

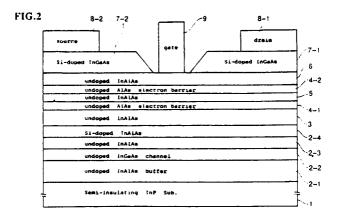
Date of deferred publication of the search report: 07.06.95 Bulletin 95/23

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- 54) Field effect transistor with a Schottky gate.
- The invention provides a Schottky barrier structure comprising a Schottky gate electrode (9), a first layer (6) in contact with said Schottky gate electrode and said first layer being made of a first compound semiconductor and a second layer (4-2) in contact

with said first layer and said second layer being made of a second compound semiconductor having a higher conduction band edge than a conduction band edge of said first compound semiconductor.



EUROPEAN SEARCH REPORT

Application Number EP 94 10 8463

Category	Citation of document with indic of relevant passa		Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int.Cl.5)
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Place of search		Date of completion of the search	Examiner Baillet, B	
Y:pa:	THE HAGUE CATEGORY OF CITED DOCUMENT reicularly relevant if taken alone reicularly relevant if combined with anoth cument of the same category	E : earlier patent d after the filing er D : document cited L : document cited	iple underlying the locument, but pub date I in the application for other reasons	e invention lished on, or
A: tec	chnological background on-written disclosure	& : member of the	same patent fami	ly, corresponding



EUROPEAN SEARCH REPORT

Application Number EP 94 10 8463

Category	Citation of document with indica of relevant passage	tion, where appropriate,	Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int.Cl.5)
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Place of search		Date of completion of the search	Do:	11et, B
X : par Y : par doc A : tecl O : nor	THE HAGUE CATEGORY OF CITED DOCUMENTS ticularly relevant if taken alone ticularly relevant if combined with another ument of the same category hological background howritten disclosure ermediate document	E : earlier patent after the filit D : document cit L : document cit	nciple underlying the t document, but publ ng date led in the application ed for other reasons	invention ished on, or